

## ABSTRACT OF THE DISCLOSURE

5 A semiconductor laser device is formed by laminating optical confinement layers and active layers so as to dispose each of said active layers between said optical confinement layers, wherein one of the opposite ends perpendicular to the junction planes of the individual layers in the semiconductor multi-layer film is coated with a low reflection film and the other of the ends is coated with a high reflection film, wherein the low reflection film is an  $\text{Al}_2\text{O}_3$  film having a resistivity of  $1 \times 10^{12} \Omega \cdot \text{m}$  or more, preferably  $1 \times 10^{13} \Omega \cdot \text{m}$  or more, and having a stoichiometric ratio composition, which is deposited by, for example, an electron cyclotron resonance sputtering process. The present invention has realized a semiconductor laser device exhibiting a prolonged duration of operating life and having high driving reliability, which is advantageous in that a catastrophic optical damage hardly occurs and a lowering of the optical output after driving at a constant current is suppressed, and thus, it is preferably used as an optical transmitter for the optical communication.

005160-4029960